Amendments to the Specification

Please replace the paragraph beginning on page 4, line 11, with the following rewritten paragraph.

During polishing with a slurry, defects such as microscratches may be formed on the surface of a topography. Microscratches may include scratches of any length having a width of less than about 0.5 μm. Such microscratches may have a depth of up to about 100 Å and may be relatively difficult to remove during final stages of polishing on a final pad. Such final pad polishing may be designed ~~may~~ to remove relatively little material from a topography thereby essentially "smoothing" an upper surface of the topography. Therefore, such microscratches may remain on the topography and may increase reliability failures of a device formed on the topography. For example, if conductive material resides in a microscratch that extends across a width of a dielectric material between two conductive structures, a short may be formed between the two conductive structures. Other such reliability failures may also be caused by such microscratches.

Please replace the paragraph beginning on page 22, line 1, with the following rewritten paragraph.

As shown in Fig. 7, semiconductor topography 154 will have a substantial amount of residual slurry particles 158 present on polished layer 156 subsequent to such polishing. For example, in conventional polishing processes, relatively large amounts of water are deposited onto a polishing pad during polishing to remove such residual slurry particles. Therefore, a semiconductor topography polished by such a conventional process will be substantially free of residual slurry particles. In contrast, as shown in Fig. 67, semiconductor topography 154 may have thousands of residual slurry particles 158 present on the topography depending on the size of the semiconductor topography.

Please replace the paragraph beginning on page 23, line 25, with the following rewritten paragraph.

Conventional methods ~~attempt~~ used to correct microscratches include extending the duration of final pad polishing. In addition, some conventional methods for correcting microscratches include slurry reintroduction during final pad polishing to increase the removal rate thereby attempting to correct microscratches formed on a topography. The reintroduction of slurry during a final polishing step is shown by the rapid increase in the pH of the polishing solution after portion 160 of the polishing process shown in

Fig. 9. Conventional final pad polishing, however, also involves rapid water introduction that may induce pH shock of the slurry used for the final pad polishing, as shown in the rapid decrease in the pH of the polishing solution during portion 166. Therefore, additional microscratches may be formed during final pad polishing.

Please replace the paragraph beginning on page 25, line 19, with the following rewritten paragraph.

A final polishing step may include, for example, six phases. Spin speeds of the platen and carrier may be approximately the same in the six phases and may be less than spin speeds of the platen and carrier in a primary polishing step. For example, the spin speeds in the final polishing step may be about 10 rpm to about 25 rpm. The downforce on the carrier and the back pressure on the semiconductor topography may also be approximately the same in the six phases and may be less than the downforces on the carrier and the back pressures on the semiconductor topography during a primary polishing step. Water may be deposited upon the polishing pad in relatively short dispense intervals that may include every other phase of the polishing (i.e., the second, fourth, and sixth phases). In an embodiment, each of the dispense intervals may have a dispense time of less than about 30 seconds. In an additional embodiment, one or more of the dispense intervals may have a dispense time of less than about 3 ~~second~~seconds, or even about 1 second. In a further embodiment, the first several dispense intervals may have shorter dispense times than later dispense intervals. For example, the second and fourth phases of the above described process may have dispense times of less about 1 second while the sixth phase may have a dispense time of about 30 seconds. Furthermore, a final polishing step may include any number of such phases. In addition, the flowrates, spin speeds, downforces, and durations described above may also vary depending upon, for example, the type of material being polished and an initial thickness of upper layer 152.